

Practice 12:

Dynamic Logic

Dynamic Operation of Digital Circuits

Static Logic Operation

- ▶ **Static Logic:**

- ▶ At all stable states (i.e. '1' and '0'), there is a ***low resistance path*** to one of the supplies.
- ▶ This ensures fast replenishment of the stable state in the event of a Single Event Upset (SEU)

- ▶ **However:**

- ▶ For CMOS we need $2n$ Transistors to implement the function.
- ▶ Changing logic states requires a full charge/discharge of the output capacitance.
- ▶ Therefore, CMOS has a relatively long delay.

Dynamic Logic Concept

- ▶ **Dynamic Operation:**

- ▶ The state of a node is stored on a capacitor.
- ▶ Some (or all) of the steady states have **high resistance** to *both* of the supply rails.

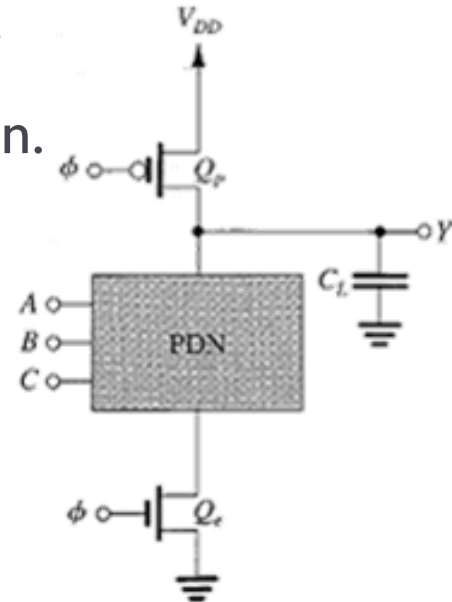
- ▶ **Faster operation is achieved by:**

- ▶ Precharging or Pre-discharging a data node's capacitance.
- ▶ Conditionally changing the state after the operation starts.
- ▶ This is applicable in *synchronous* circuits that are *clocked*.

Dynamic CMOS Logic

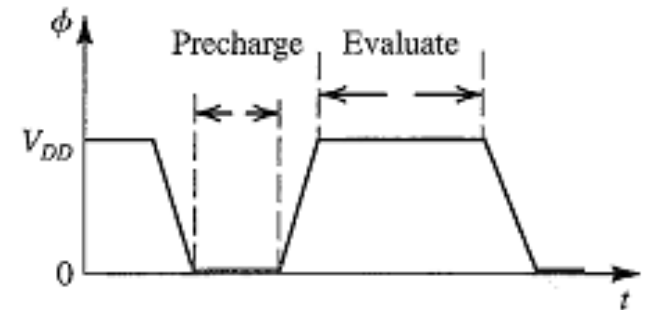
- ▶ n-type Dynamic CMOS Logic is constructed of:

- ▶ A PDN that implements the (*inverting*) logic function.
- ▶ A pMOS *precharge* transistor.
- ▶ An nMOS *evaluation* transistor.



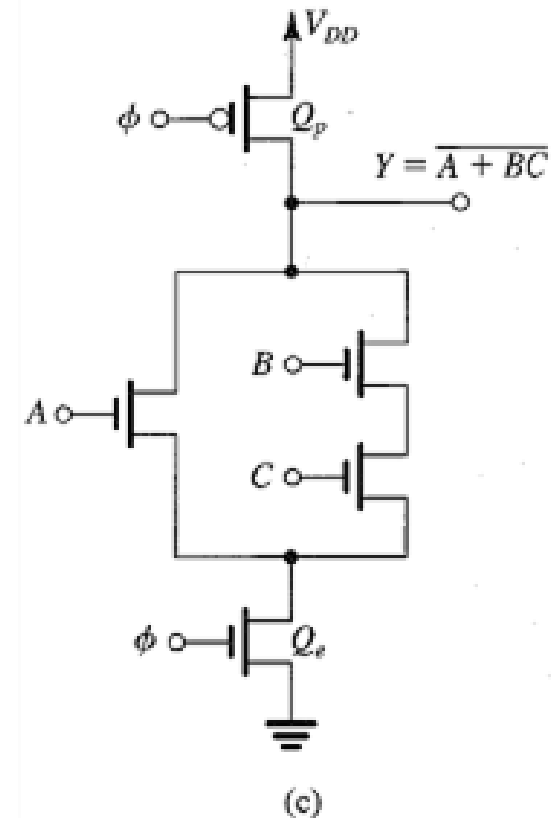
- ▶ The clock phase is divided into:

- ▶ “Precharge” – During which the output is charged to V_{DD} .
- ▶ “Evaluate” – During which the output is conditionally discharged.



Properties of Dynamic CMOS

- ▶ N+2 Transistors.
- ▶ Non-Ratioed.
- ▶ Zero Static Power.
- ▶ Zero Short Circuit Power
- ▶ High Operation Speed:
 - ▶ $t_{pLH}=0$
 - ▶ $C_{out}(\text{Dynamic}) < C_{out}(\text{CMOS})$
 - ▶ $I_{SC}=0$
 - ▶ Minimal Self Loading effect
- ▶ But Dynamic Energy is high:
 - ▶ $P(0 \rightarrow 1 | out=0)=1$



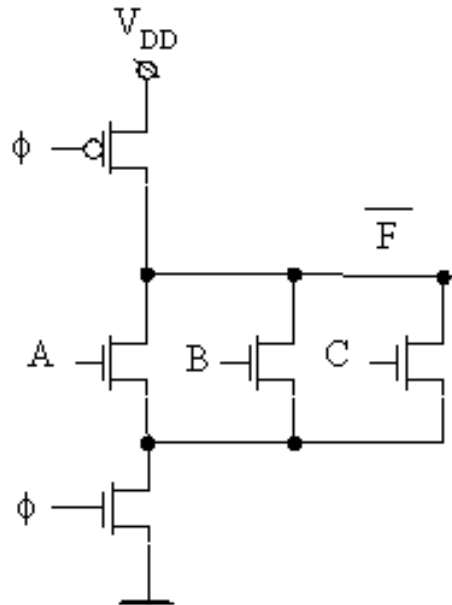
Exercise 1: Cascading Problem

Exercise 1a

- ▶ A. Implement the following two functions with Dynamic CMOS Logic:

$$f = A + B + C \quad g = A + B + C + D$$

- ▶ First we will implement the function f :



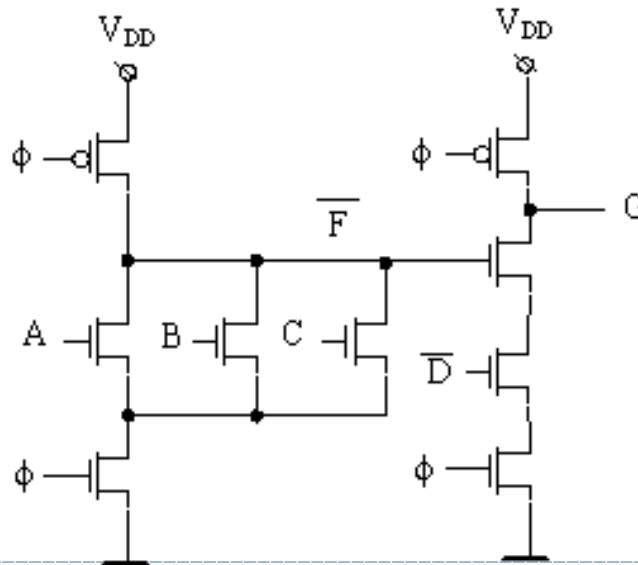
Exercise 1a

- ▶ A. Implement the following two functions with Dynamic CMOS Logic:

$$f = A + B + C \quad g = A + B + C + D$$

- ▶ Now we can just easily create g .

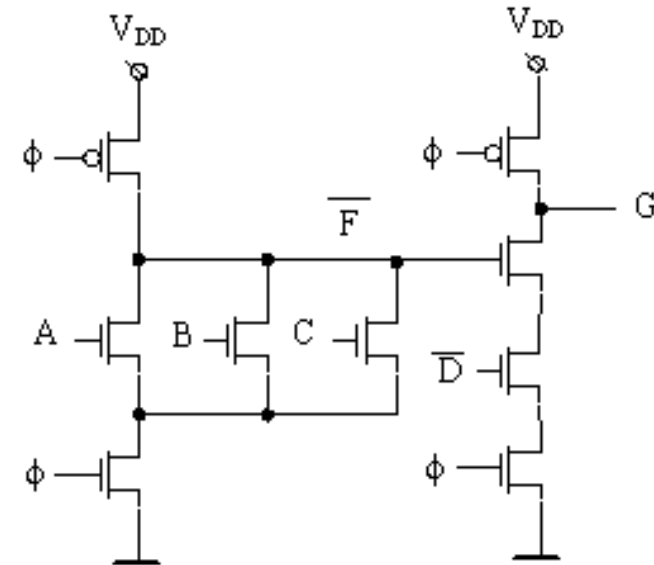
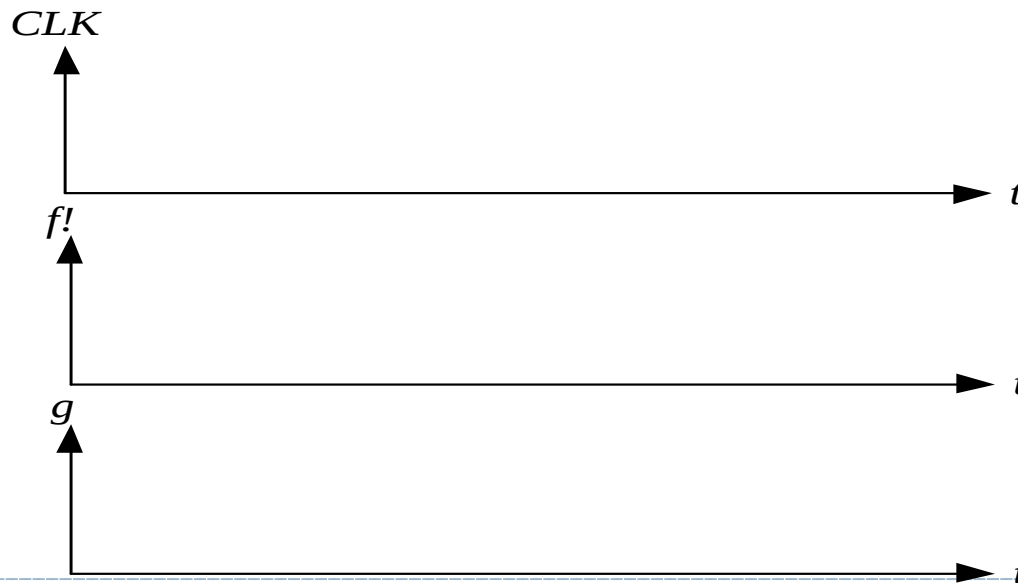
$$g = A + B + C + D = \overline{\overline{A + B + C} \cdot \overline{D}} = \overline{\overline{f} \cdot \overline{D}}$$



Exercise 1b

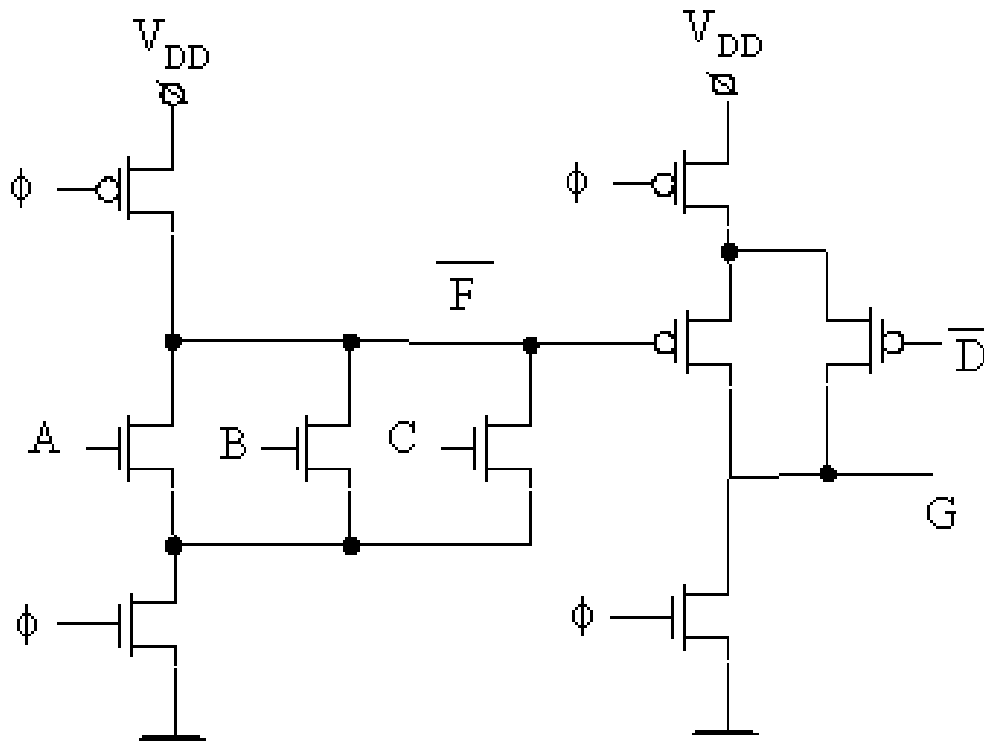
► B. Does this gate work???

- Let's look at the case where $f=0$ (A or B or $C=1$) and $D=0$
- During PC, $F!=1$, $G=1$
- When the clock rises, $F!$ discharges.
- But until it does, G discharges.
- Nothing can replenish G !!!



Exercise 1c

- ▶ C. Use the np-CMOS concept to fix this gate.
- ▶ We can implement the second stage with a pre-discharge and a PUN.



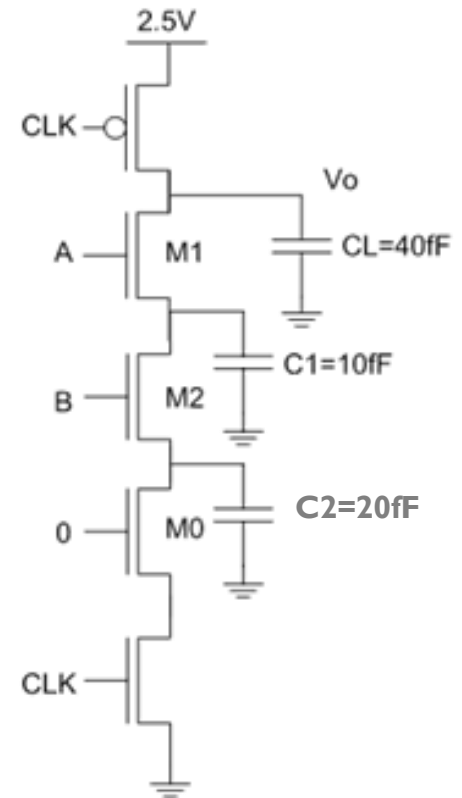
Exercise 2: Charge Sharing Problem

Exercise 2a

$$V_{DD} = 2.5 \quad V_{t0} = 0.55V$$

$$2\Phi_F = 0.6V \quad \gamma = 0.4\sqrt{V}$$

- ▶ A. Given a NAND3 gate as follows:
 - ▶ Assume all internal nodes are at 0V during precharge.
 - ▶ At $t < 0$ (precharge), $A=B=0$
 - ▶ At $t > 0$ (evaluation), A and B rise ($0 \rightarrow 1$)
- ▶ Find the voltage drop at V_{out} .



Exercise 2a

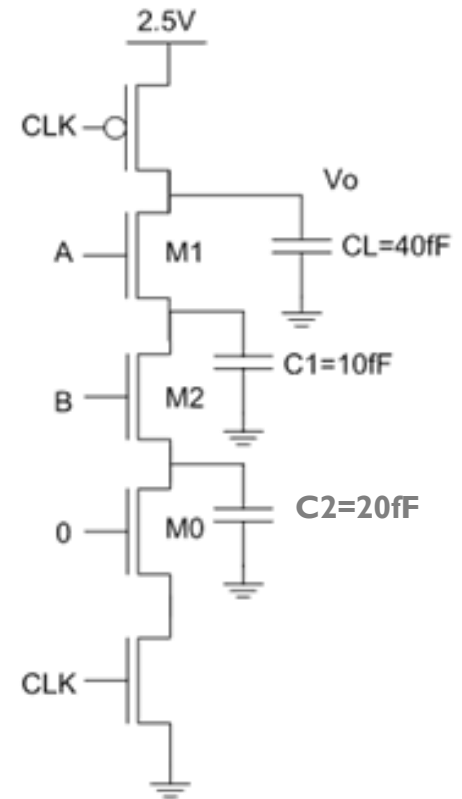
$$V_{DD} = 2.5 \quad V_{t0} = 0.55V$$
$$2\Phi_F = 0.6V \quad \gamma = 0.4\sqrt{V}$$

- ▶ After A and B rise, we have charge sharing between CL and C1+C2.

- ▶ According to charge conservation:

$$Q_{initial} = C_L V_{DD} = Q_{final} = (C_L + C_1 + C_2) V_{final}$$

$$V_{final} = \frac{C_L}{C_L + C_1 + C_2} V_{DD} = \frac{40f}{70f} 2.5 = 1.42V$$



Exercise 2b

$$V_{DD} = 2.5 \quad V_{t0} = 0.55V$$

$$2\Phi_F = 0.6V \quad \gamma = 0.4\sqrt{V}$$

- ▶ What if only A rose from 0 → 1?

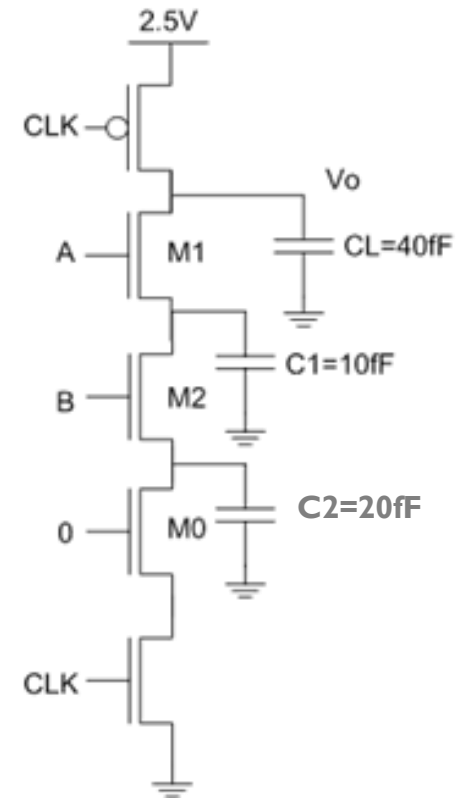
- ▶ From the previous solution:

$$V_{final} = \frac{C_L}{C_L + C_1} V_{DD} = \frac{40f}{50f} 2.5 = 2V$$

- ▶ But pay close attention...

$$V_{GS}(M1) = V_{DD} - V_{final} = 0.5V < V_{t0}$$

- ▶ Therefore, M1 turns off before the charge share is complete!



Exercise 2b

$$V_{DD} = 2.5 \quad V_{t0} = 0.55V$$

$$2\Phi_F = 0.6V \quad \gamma = 0.4\sqrt{V}$$

- To calculate the exact point, we need to take into account the body effect:

$$V_{SB}(M1) = V_{C1} = V_{DD} - V_{t,final}$$

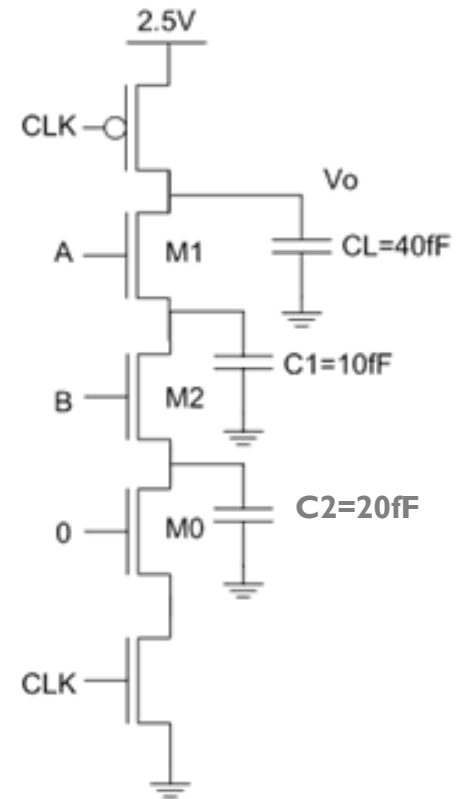
$$V_{t,final} = V_{t0} + \gamma \left(\sqrt{|2\Phi_F + (V_{DD} - V_{t,final})|} - \sqrt{|2\Phi_F|} \right)$$

$$= 0.55 + 0.4 \left(\sqrt{|0.6 + 2.5 - V_{t,final}|} - \sqrt{0.6} \right)$$

$$V_{t,final} - 0.25 = 0.4 \sqrt{3.1 - V_{t,final}}$$

$$V_{t,final}^2 - 0.5V_{t,final} + 0.0625 = 0.496 - 0.16V_{t,final}$$

$$V_{t,final} = 0.85V \quad V_{C1} = V_{DD} - V_{t,final} = 1.65V$$



Exercise 2b

$$V_{DD} = 2.5 \quad V_{t0} = 0.55V$$

$$2\Phi_F = 0.6V \quad \gamma = 0.4\sqrt{V}$$

- Now we can find the final output voltage:

$$Q_{initial} = C_L V_{DD} = Q_{final} = C_L V_{final} + C_1 V_{C1}$$

$$V_{final} = \frac{C_L V_{DD} - C_1 V_{C1}}{C_L} = \frac{40 f \cdot 2.5 - 10 f \cdot 1.65}{40 f} = 2.0875V$$

